

## ULTRA-FAST RECOVERY RECTIFIER DIODES

### MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	5 A
$V_{RRM}$	200 V
$T_j(\max)$	150°C
$V_F(\max)$	0.99 V
$t_{rr}(\max)$	30 ns

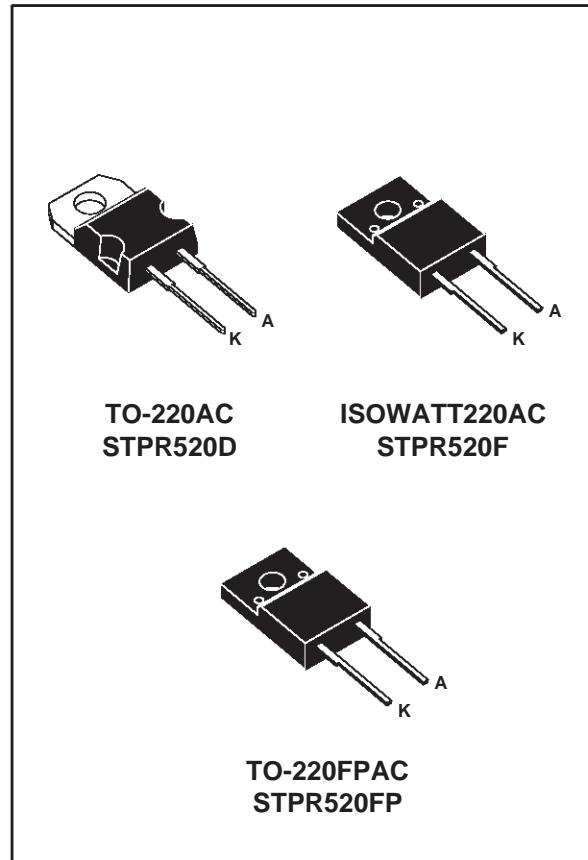
### FEATURES

- Suited for SMPS
- Very low forward losses
- Negligible switching losses
- High surge current capability
- Insulated packages:  
ISOWATT220AC / TO-220FPAC  
Insulation voltage = 2000V DC  
Capacitance = 12pF

### DESCRIPTION

Low cost single chip rectifier suited for Switch Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-220AC, ISOWATT220AC and TO-220FPAC, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



Symbol	Parameter			Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage			200	V
$I_{F(RMS)}$	RMS forward current			10	A
$I_{F(AV)}$	$\delta = 0.5$	TO-220AC	$T_c = 125^\circ\text{C}$	5	A
		ISOWATT220AC TO-220FPAC	$T_c = 115^\circ\text{C}$		
$I_{FSM}$	Surge non repetitive forward current		$T_p = 10 \text{ ms}$ Sinusoidal	50	A
$T_{stg}$	Storage temperature range			- 65 to + 150	°C
$T_j$	Maximum operating junction temperature			+ 150	

## STPR520D/F/FP

### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AC	4	$^{\circ}\text{C/W}$
		ISOWATT220AC / TO-220FPAC	6	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameters	Test conditions		Min.	Typ.	Max.	Unit
$I_R$ *	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			50	$\mu\text{A}$
		$T_j = 100^{\circ}\text{C}$				0.5	$\text{mA}$
$V_F$ **	Forward voltage drop	$T_j = 125^{\circ}\text{C}$	$I_F = 5 \text{ A}$			0.99	$\text{V}$
		$T_j = 125^{\circ}\text{C}$	$I_F = 10 \text{ A}$			1.20	
		$T_j = 25^{\circ}\text{C}$	$I_F = 10 \text{ A}$			1.25	

Pulse test : \*  $t_p = 5 \text{ ms}, \delta < 2 \%$

\*\*  $t_p = 380 \mu\text{s}, \delta < 2 \%$

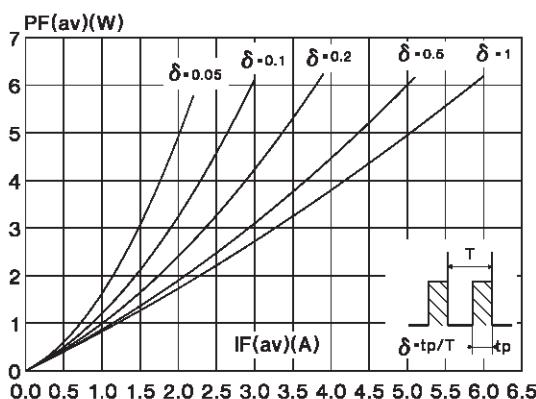
To evaluate the conduction losses use the following equation :

$$P = 0.78 \times I_{F(AV)} + 0.042 \times I_{F}^2(\text{RMS})$$

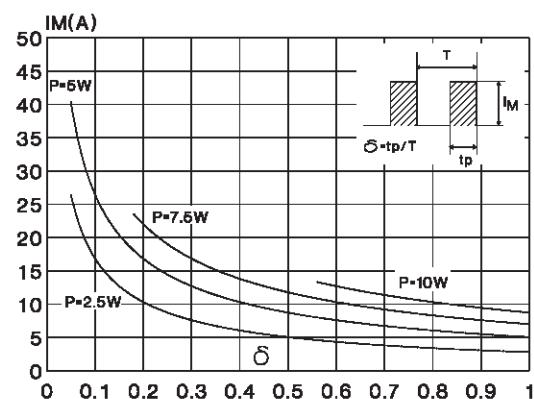
### RECOVERY CHARACTERISTICS

Symbol	Test conditions			Min.	Typ.	Max.	Unit
$trr$	$T_j = 25^{\circ}\text{C}$	$I_F = 0.5 \text{ A}$	$I_{rr} = 0.25 \text{ A}$	$I_R = 1 \text{ A}$		30	$\text{ns}$
$tfr$	$T_j = 25^{\circ}\text{C}$	$I_F = 1 \text{ A}$	$tr = 10 \text{ ns}$			20	
$V_{FP}$	$T_j = 25^{\circ}\text{C}$	$I_F = 1 \text{ A}$	$tr = 10 \text{ ns}$			3	$\text{V}$

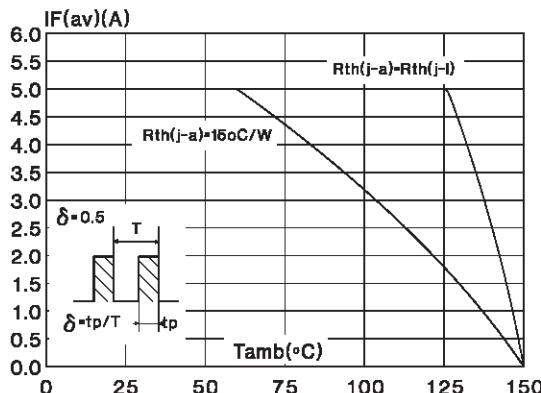
**Fig. 1:** Average forward power dissipation versus average forward current.



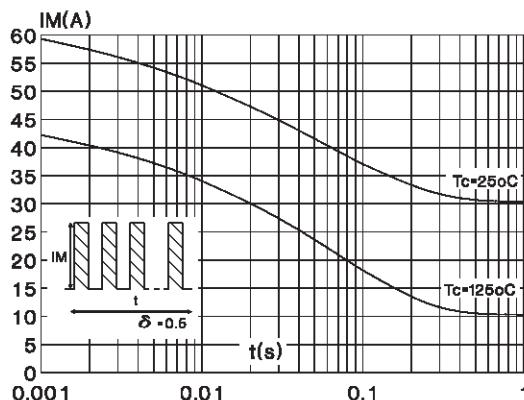
**Fig. 2:** Peak current versus form factor.



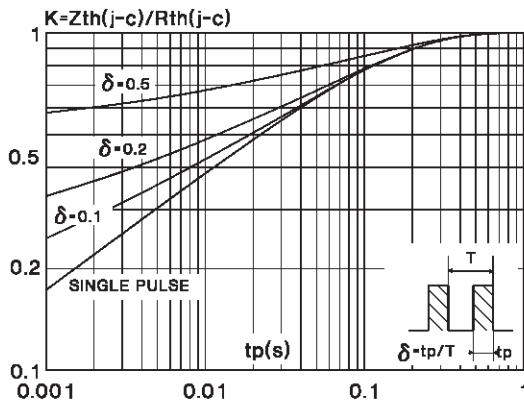
**Fig. 3:** Average current versus ambient temperature.



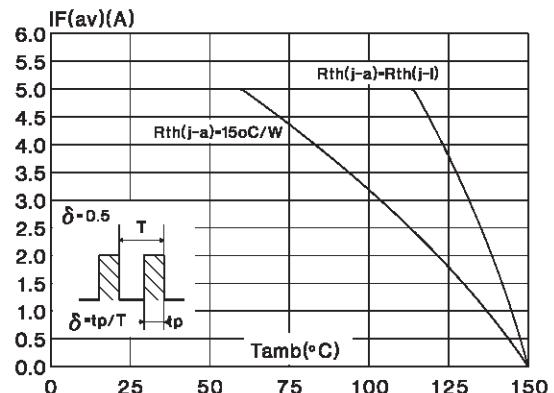
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values) (TO-220AC).



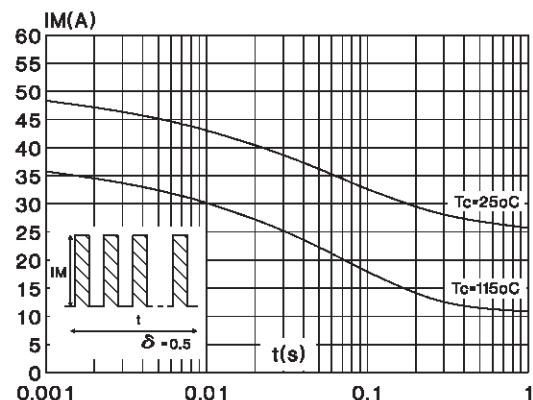
**Fig. 7:** Relative variation of thermal transient impedance junction to case versus pulse duration (TO-220AC).



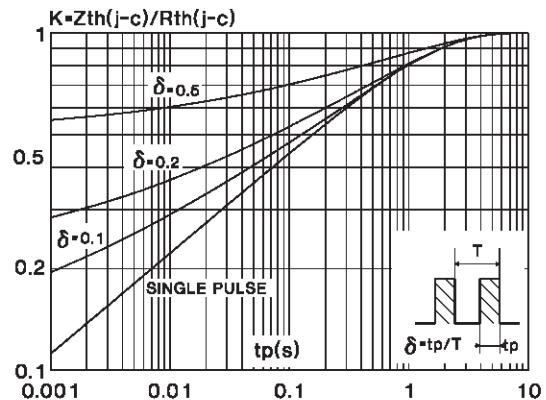
**Fig. 4:** Average current versus ambient temperature.



**Fig. 6:** Non repetitive surge peak forward current versus overload duration (maximum values) (ISOWATT220AC, TO-220FPAC).

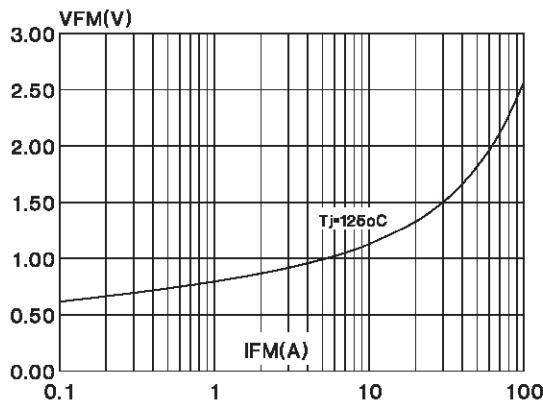


**Fig. 8:** Relative variation of thermal transient impedance junction to case versus pulse duration (ISOWATT220AC, TO-220FPAC).

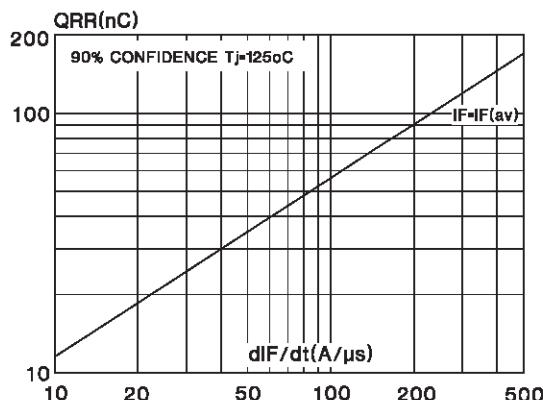


## STPR520D/F/FP

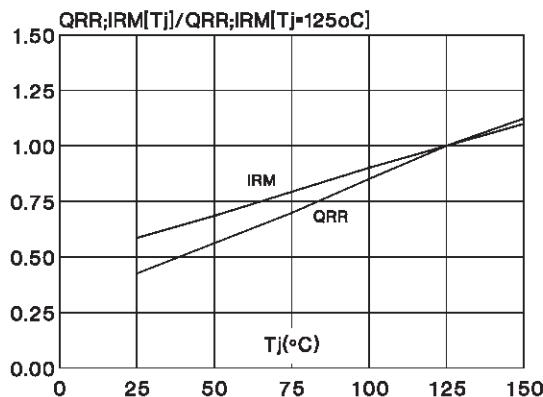
**Fig. 9:** Forward voltage drop versus forward current.



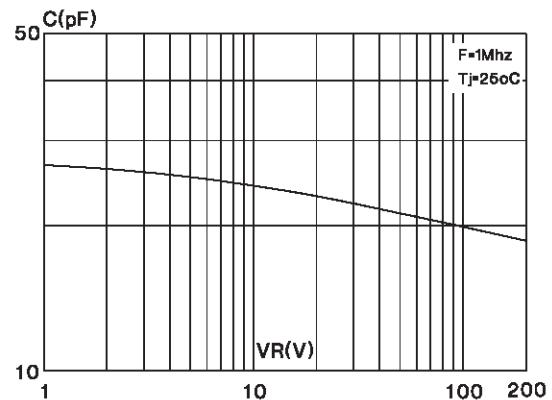
**Fig. 11:** Recovery charge versus  $dI_F/dt$ .



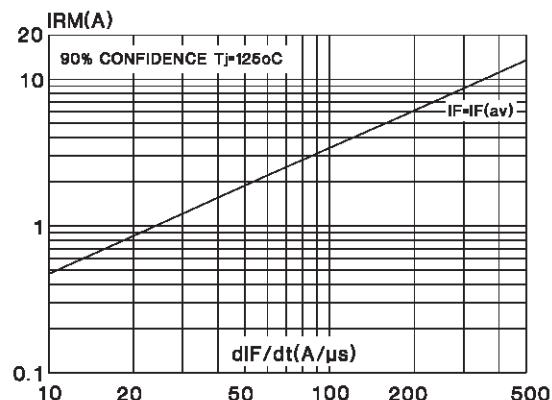
**Fig. 13:** Dynamic parameters versus junction temperature.



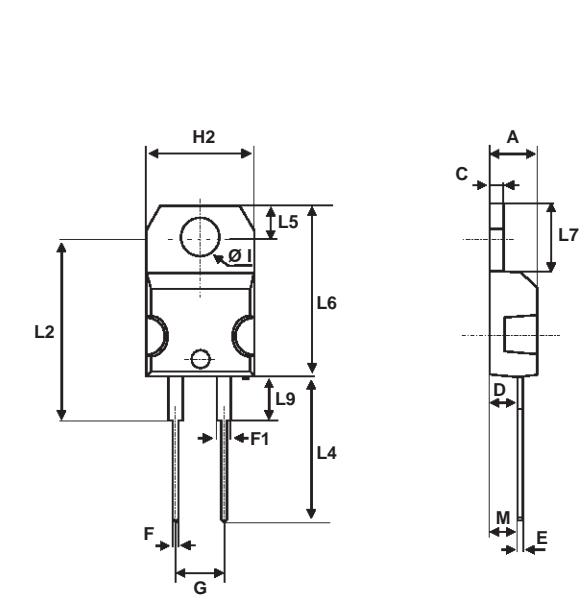
**Fig. 10:** Junction capacitance versus reverse voltage applied (typical values).



**Fig. 12:** Peak reverse current versus  $dI_F/dt$ .

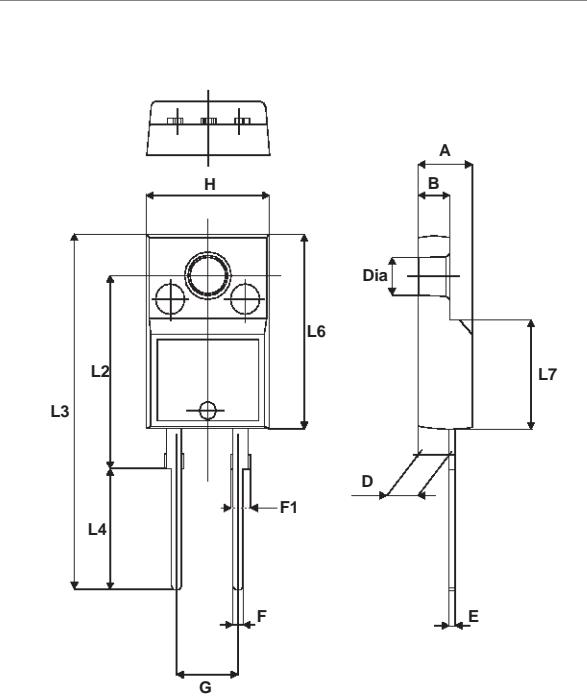


**PACKAGE MECHANICAL DATA**  
TO-220AC



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam. I	3.75	3.85	0.147	0.151

**PACKAGE MECHANICAL DATA**  
TO-220FPAC



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.9	0.173	0.193
B	2.5	2.9	0.098	0.106
D	2.45	2.75	0.096	0.108
E	0.40	0.70	0.016	0.027
F	0.60	1	0.024	0.039
F1	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.204
H	10	10.7	0.393	0.421
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.204
L4	9.8	10.7	0.385	0.421
L6	15.8	16.4	0.622	0.645
L7	9.00	9.90	0.354	0.389
Dia.	2.9	3.50	0.118	0.138

## STPR520D/F/FP

### PACKAGE MECHANICAL DATA ISOWATT220AC

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
B	2.50	2.70	0.098	0.106
D	2.40	2.75	0.094	0.108
E	0.40	0.70	0.016	0.028
F	0.75	1.00	0.030	0.039
F1	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
H	10.00	10.40	0.394	0.409
L2	16.00 Typ.		0.630 Typ.	
L3	28.60	30.60	1.125	1.205
L6	15.90	16.40	0.626	0.646
L7	9.00	9.30	0.354	0.366
Diam	3.00	3.20	0.118	0.126

- Cooling method: by conduction (C)
- Recommended torque value (ISOWATT220AC, TO-220FPAC): 0.55 nm
- Maximum torque value (ISOWATT220AC, TO-220FPAC): 0.7 Nm
- Recommended torque value (TO-220AC): 0.8 Nm
- Maximum torque value (TO-220AC): 1.0 Nm
- Epoxy meets UL94, V0

Type	Marking	Package	Weight	Base Qty	Delivery mode
STPR520D	STPR520D	TO-220AC	2.3 g	50	Tube
STPR520F	STPR520F	ISOWATT220AC	2 g	50	Tube
STPR520FP	STPR520FP	TO-220FPAC	1.8 g	50	Tube

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